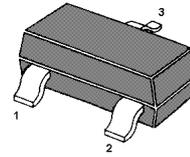
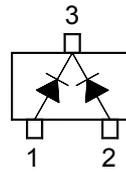


MMBD6100

Silicon Epitaxial Planar Switching Diode

Features

- Small package
- Low forward voltage
- Fast reverse recovery time
- Small total capacitance



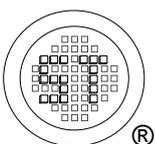
Marking Code: **A4**
TO-236 Plastic Package

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Reverse Voltage	V_R	70	V
Forward Current	I_F	200	mA
Maximum Peak Forward Current	I_{FM}	300	mA
Non-Repetitive Peak Forward Surge Current	I_{FSM}	1 2	A
		at $t = 1\text{ s}$ at $t = 1\text{ }\mu\text{s}$	
Power Dissipation	P_{tot}	300	mW
Thermal Resistance Junction to Ambient Air	$R_{\theta JA}$	417	$^\circ\text{C/W}$
Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

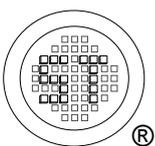
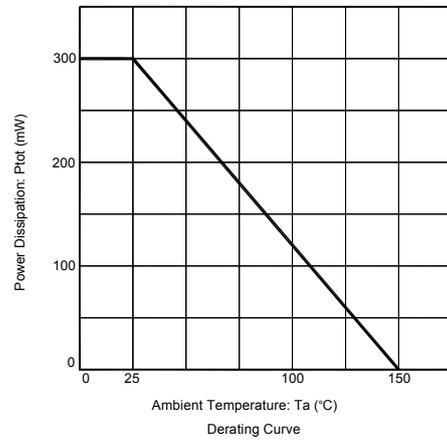
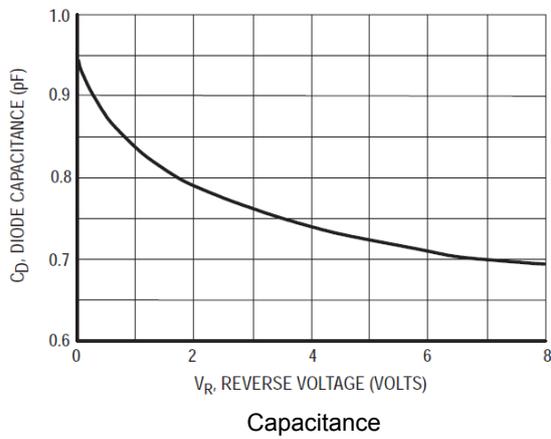
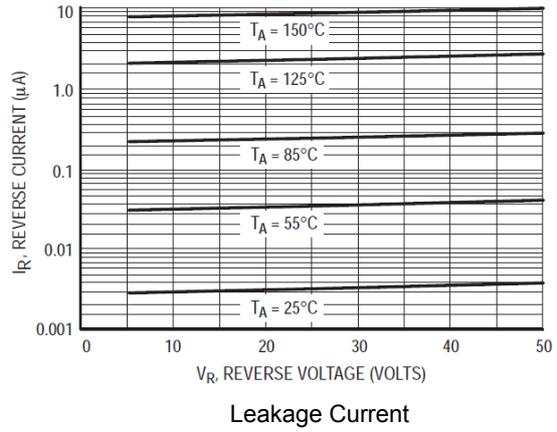
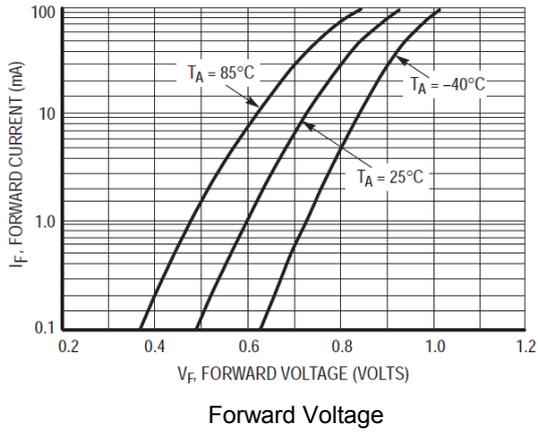
Parameter	Symbol	Min.	Max.	Unit
Forward Voltage	V_F	0.55 0.85	0.7 1.1	V
		at $I_F = 1\text{ mA}$ at $I_F = 100\text{ mA}$		
Reverse Current	I_R	-	0.1	μA
		at $V_R = 50\text{ V}$		
Reverse Breakdown Voltage	$V_{(BR)R}$	70	-	V
		at $I_R = 100\text{ }\mu\text{A}$		
Total Capacitance	C_T	-	2.5	pF
		at $V_R = 0$		
Reverse Recovery Time	t_{rr}	-	4	ns
		at $I_F = I_R = 10\text{ mA}$		



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